

wherein an insulating film formed on the first, second and third MOS transistors, the insulating film having contact holes reaching the sources and drains of the first, second and third MOS transistors,

*BB1*  
a silicide film is not formed on a surface of the drain of the first MOS transistor, but the silicide film is formed on each surface of the sources and drains of the first, second and third MOS transistors except for the drain of the first MOS transistor.

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**Please add new claims 14 and 15 as follows:**

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14. A CMOS image sensor comprising:

*BB2*  
a photodiode having an impurity region formed by introducing impurities into the semiconductor substrate;

first and second MOS transistors having source regions and drain regions formed respectively by introducing impurities into the semiconductor substrate; and

an insulating film formed on the first and second MOS transistors, the insulating film having contact holes reaching the source regions and drain regions of the first and second MOS transistors,

wherein a silicon oxide film is formed on a surface of the impurity region of the photodiode and the drain region of the first MOS transistor which connects to the impurity region of the photodiode, but a silicide film is formed on a surface of the source region of the first MOS transistor which is also the drain region of the second MOS transistor and on a surface of the drain region of the second MOS transistor.

15. AS CMOS image sensor comprising:

a photodiode having an impurity region formed by introducing impurities into the semiconductor substrate;

first and second MOS transistors having source regions and drain regions formed respectively by introducing impurities into the semiconductor substrate; and

an insulating film formed on the first and second MOS transistors, the insulating film having contact holes reaching the source regions and drain regions of the first and second MOS transistors,

*B62*  
wherein a silicon oxide film is formed on a surface of the impurity region of the photodiode and the drain region of the first MOS transistor which connects to the impurity region of the photodiode, but a silicide film is formed on a surface of the source region of the first MOS transistor which is also the drain region of the second MOS transistor and on a surface of the drain region of the second MOS transistor, and

a concentration of the impurity region of the photodiode differs from that of the drain region of the first MOS transistor.